ESD Protection Diode

Low Capacitance Array for High Speed Data Lines

ESD8704

The ESD8704 is designed to protect high speed data lines from ESD. Ultra-low capacitance and low ESD clamping voltage make this device an ideal solution for protecting voltage sensitive high speed data lines. The flow-through style package allows for easy PCB layout and matched trace lengths necessary to maintain consistent impedance between high speed differential lines such as USB 3.0/3.1.

Features

- Low Capacitance (0.5 pF Max, I/O to GND)
- Protection for the Following IEC Standards: IEC 61000-4-2 (Level 4)
- Low ESD Clamping Voltage
- SZESD8704MTWTAG Wettable Flank Package for optimal Automated Optical Inspection (AOI)
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- USB 3.0/3.1
- eSATA
- DisplayPort

MAXIMUM RATINGS (T_J = 25° C unless otherwise noted)

Rating	Symbol	Value	Unit
Operating Junction Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Lead Solder Temperature – Maximum (10 Seconds)	ΤL	260	°C
IEC 61000-4-2 Contact (ESD) IEC 61000-4-2 Air (ESD)	ESD ESD	±30 ±30	kV kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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MARKING DIAGRAM



7D M•

7D

- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

UDFN10

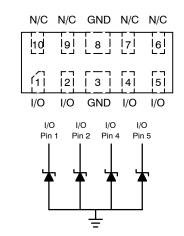
CASE 517BB

= Specific Device Code

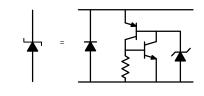


AAA = Specific Device Code M = Date Code

PIN CONFIGURATION AND SCHEMATIC



Pins 3, 8 Note: Common GND – Only Minimum of 1 GND connection required



ORDERING INFORMATION

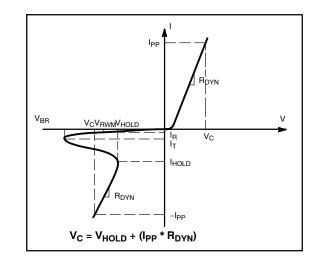
See Application Note AND8308/D for further description of survivability specs.

See detailed ordering, marking and shipping information in the package dimensions section on page 9 of this data sheet.

ELECTRICAL CHARACTERISTICS

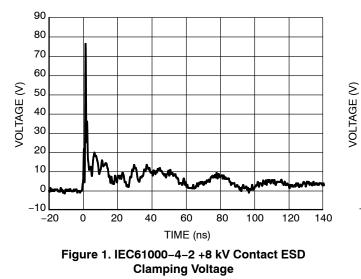
(T_A = 25°C unless otherwise noted)

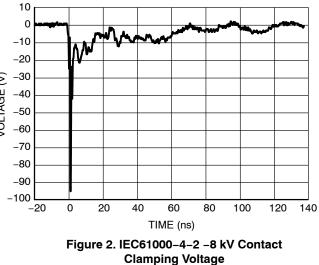
Symbol	Parameter
V _{RWM}	Working Peak Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
Ι _Τ	Test Current
V _{HOLD}	Holding Reverse Voltage
I _{HOLD}	Holding Reverse Current
R _{DYN}	Dynamic Resistance
I _{PP}	Maximum Peak Pulse Current
V _C	Clamping Voltage @ I _{PP} V _C = V _{HOLD} + (I _{PP} * R _{DYN})



Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	V _{RWM}	I/O Pin to GND			3.3	V
Breakdown Voltage	V _{BR}	I _T = 1 mA, I/O Pin to GND		5.0	6.0	V
Reverse Leakage Current	I _R	V _{RWM} = 3.3 V, I/O Pin to GND			1.0	μA
Holding Reverse Voltage	V _{HOLD}	I/O Pin to GND		1.9		V
Holding Reverse Current	I _{HOLD}	I/O Pin to GND		20		mA
Clamping Voltage	V _C	IEC61000-4-2, ±8 KV Contact				V
Clamping Voltage TLP	V _C	I _{PP} = 8 A I _{PP} = -8 A		4.7 -4.0		V
		I _{PP} = 16 A I _{PP} = –16 A		6.6 -6.7		
Dynamic Resistance	R _{DYN}	I/O Pin to GND GND to I/O Pin		0.30 0.38		Ω
Junction Capacitance	CJ	$ \begin{array}{l} V_R = 0 \; V, \; f = 1 \; MHz \; \text{between I/O Pins and GND} \\ V_R = 0 \; V, \; f = 2.5 \; \text{GHz} \; \text{between I/O Pins and GND} \\ V_R = 0 \; V, \; f = 5.0 \; \text{GHz} \; \text{between I/O Pins and GND} \\ V_R = 0 \; V, \; f = 1 \; \text{MHz}, \; \text{between I/O Pins} \end{array} $		0.30 0.30 0.31 0.15	0.50 0.40 0.40 0.25	pF

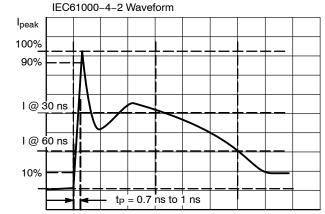
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

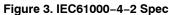




IEC 61000-4-2 Spec.

Level	Test Volt- age (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8





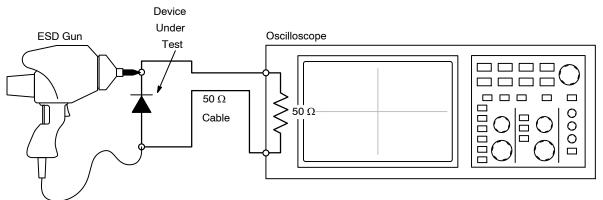


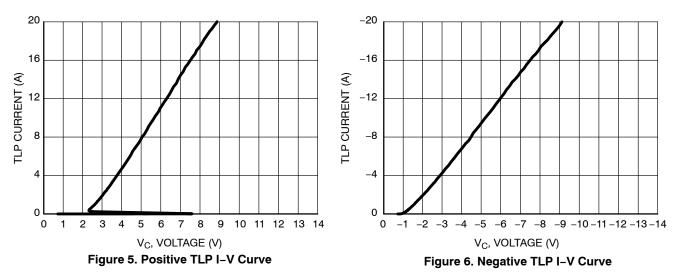
Figure 4. Diagram of ESD Clamping Voltage Test Setup

The following is taken from Application Note AND8307/D – Characterization of ESD Clamping Performance.

ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000–4–2 waveform. Since the IEC61000–4–2 was written as a pass/fail spec for larger

systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.



NOTE: TLP parameter: Z₀ = 50 Ω, t_p = 100 ns, t_r = 300 ps, averaging window: t₁ = 30 ns to t₂ = 60 ns. V_{IEC} is the equivalent voltage stress level calculated at the secondary peak of the IEC 61000–4–2 waveform at t = 30 ns with 2 A/kV. See TLP description below for more information.

Transmission Line Pulse (TLP) Measurement

Transmission Line Pulse (TLP) provides current versus voltage (I–V) curves in which each data point is obtained from a 100 ns long rectangular pulse from a charged transmission line. A simplified schematic of a typical TLP system is shown in Figure 7. TLP I–V curves of ESD protection devices accurately demonstrate the product's ESD capability because the 10s of amps current levels and under 100 ns time scale match those of an ESD event. This is illustrated in Figure 8 where an 8 kV IEC 61000–4–2 current waveform is compared with TLP current pulses at 8 A and 16 A. A TLP I–V curve shows the voltage at which the device turns on as well as how well the device clamps voltage over a range of current levels. For more information on TLP measurements and how to interpret them please refer to AND9007/D.

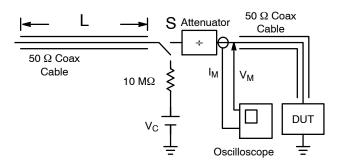


Figure 7. Simplified Schematic of a Typical TLP System

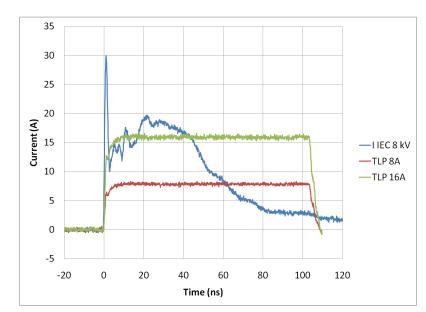
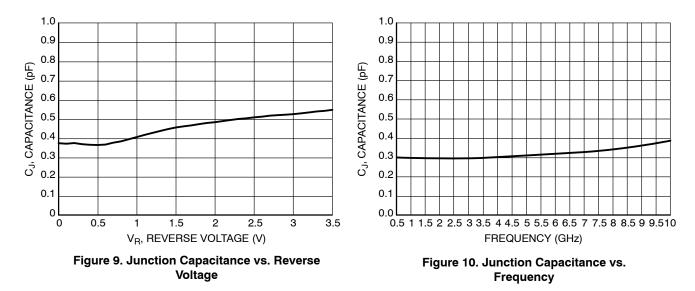
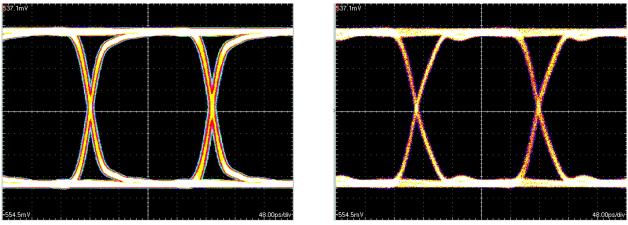


Figure 8. Comparison Between 8 kV IEC 61000-4-2 and 8 A and 16 A TLP Waveforms





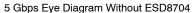
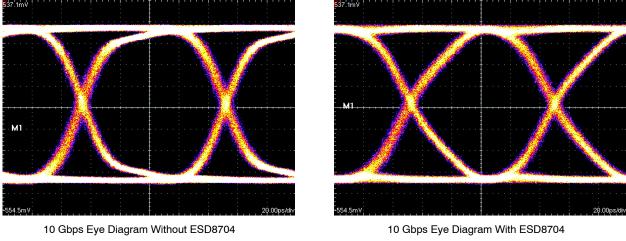




Figure 11. USB3.0 Eye Diagram with and without ESD8704. 5 Gb/s





See application note AND9075/D for further description of eye diagram testing methodology.

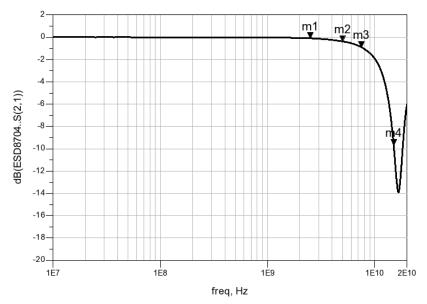


Figure 13. ESD8704 Insertion Loss

Interface	Data Rate (Gb/s)	Fundamental Frequency (GHz)	3 rd Harmonic Frequency (GHz)	ESD8704 Insertion Loss (dB)
USB 3.0	5	2.5 (m1)	7.5 (m3)	m1 = -0.09 m3 = -0.89
USB 3.1	10	5.0 (m2)	15 (m4)	m2 = -0.36 m4 = -9.68

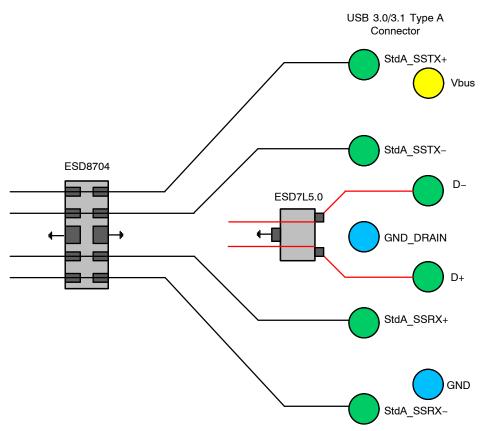


Figure 14. USB 3.0/3.1 Standard Layout Diagram

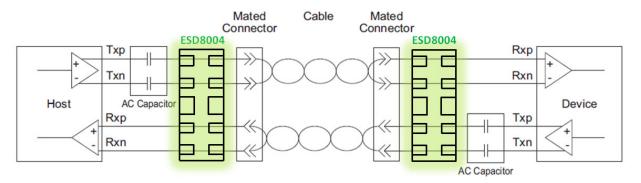
PCB Layout Guidelines

Steps must be taken for proper placement and signal trace routing of the ESD protection device in order to ensure the maximum ESD survivability and signal integrity for the application. Such steps are listed below.

- Place the ESD protection device as close as possible to the I/O connector to reduce the ESD path to ground and improve the protection performance.
 - In USB 3.0 applications, the ESD protection device should be placed between the AC coupling capacitors and the I/O connector on the TX differential lanes as shown in Figure 15. In this configuration, no DC current can flow through the ESD protection device preventing any potential

latch-up condition. For more information on latchup considerations, see below description on Page 8.

- Make sure to use differential design methodology and impedance matching of all high speed signal traces.
 - Use curved traces when possible to avoid unwanted reflections.
 - Keep the trace lengths equal between the positive and negative lines of the differential data lanes to avoid common mode noise generation and impedance mismatch.
 - Place grounds between high speed pairs and keep as much distance between pairs as possible to reduce crosstalk.

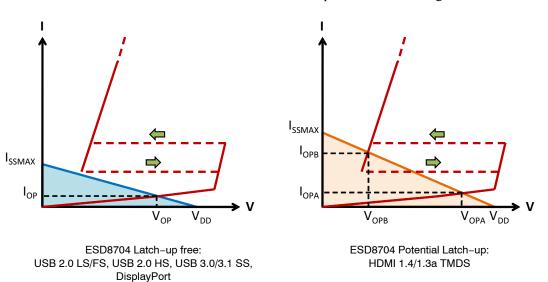




Latch-Up Considerations

ON Semiconductor's 8000 series of ESD protection devices utilize a snap-back, SCR type structure. By using this technology, the potential for a latch-up condition was taken into account by performing load line analyses of common high speed serial interfaces. Example load lines for latch-up free applications and applications with the potential for latch-up are shown below with a generic IV characteristic of a snapback, SCR type structured device overlaid on each. In the latch-up free load line case, the IV characteristic of the snapback protection device intersects the load-line in one unique point (V_{OP} I_{OP}). This is the only stable operating point of the circuit and the system is

therefore latch-up free. Please note that for USB 3.0 applications, ESD8704 latch-up free considerations are explained in more detail in the above PCB layout guidelines. In the non-latch up free load line case, the IV characteristic of the snapback protection device intersects the load-line in two points (V_{OPA}, I_{OPA}) and (V_{OPB}, I_{OPB}). Therefore in this case, the potential for latch-up exists if the system settles at (V_{OPB}, I_{OPB}) after a transient. Because of this, ESD8704 should not be used for HDMI applications – ESD8104 or ESD8040 have been designed to be acceptable for HDMI application Note AND9116/D for a more in-depth explanation of latch-up considerations using ESD8000 series devices.



Application	VBR (min) (∨)	IH (min) (mA)	VH (min) (∨)	ON Semiconductor ESD8000 Series Recommended PN
HDMI 1.4/1.3a TMDS	3.465	54.78	1.0	ESD8104, ESD8040
USB 2.0 LS/FS	3.301	1.76	1.0	ESD8704
USB 2.0 HS	0.482	N/A	1.0	ESD8704
USB 3.0/3.1 SS	2.800	N/A	1.0	ESD8704, ESD8006
DisplayPort	3.600	25.00	1.0	ESD8704, ESD8006

Table 1. SUMMARY OF SCR REQUIREMENTS FOR LATCH-UP FREE APPLICATIONS

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
ESD8704MUTAG	7D	UDFN10 (Pb-Free)	3000 / Tape & Reel
SZESD8704MUTAG	7D	UDFN10 (Pb-Free)	3000 / Tape & Reel
SZESD8704MTWTAG	AAA	WDFNW10 (Pb-Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



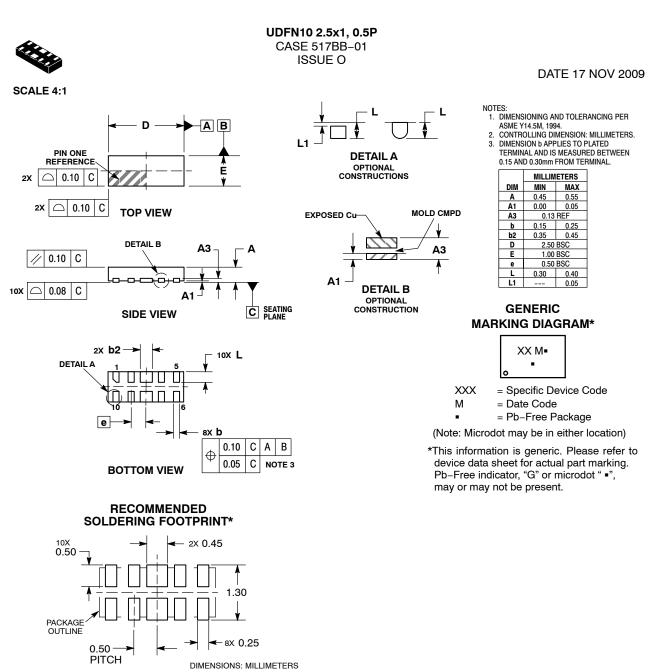
	WDFNW10 2.5x1.0, 0.5P CASE 515AH ISSUE B				
				DATE 03	AUG 2020
	NDTES	ı			
		MENSIONIN ME Y14.5M,		ERANCING	PER
		ONTROLLIN	G DIMENSI	IN: MILLIM	ETERS
				ES TO PLA	
TOP VIEW		RMINALS A 5 AND 0.30			
	PLATED 4. C	DPLANARIT			
DETAIL B		D AS WELI	L AS THE	TERMINALS	S.
	DE	HIS DE∨ICI SIGN FEAT IRMATI⊡N D	URES TO	AID IN FIL	
	TING		MI	LLIMETE	RS
NOTE 4 SIDE VIEW	ANE .	DIM	MIN.	NDM.	MAX.
		Α	0.70	0.75	0.80
		A1	0.00		0.05
		A3	ĺ	0.20 REF	-
		A4	0.10		
		b	0.15	0.20	0.25
		b2	0.35	0.40	0.45
BOTTOM VIEW		D	2.40	2.50	2.60
2x 0.45		E	0.90	1.00	1.10
		e		0.50 BSC	
		L	0.30	0.35	0.40
		L3			0.10
RECOMMENDED	SURFACE ALTERNATE CONSTRUCTION				
MOUNTING FOOTPRINT * For additional information on our Pb-Free strategy and	DETAIL B	NJ A 1		RIC AGRAM*	
 For additional information on our forree strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SULDERRM/D. 		IVIA		agram^]	
			XXXN	1	
			0		

0 XX = Specific Device Code M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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